

**isc Silicon PNP Power Transistor**

**BD798**

**DESCRIPTION**

- Collector-Emitter Sustaining Voltage-  
:  $V_{CEO(SUS)} = -60V(\text{Min})$
- Low Saturation Voltage
- Complement to Type BD797

**APPLICATIONS**

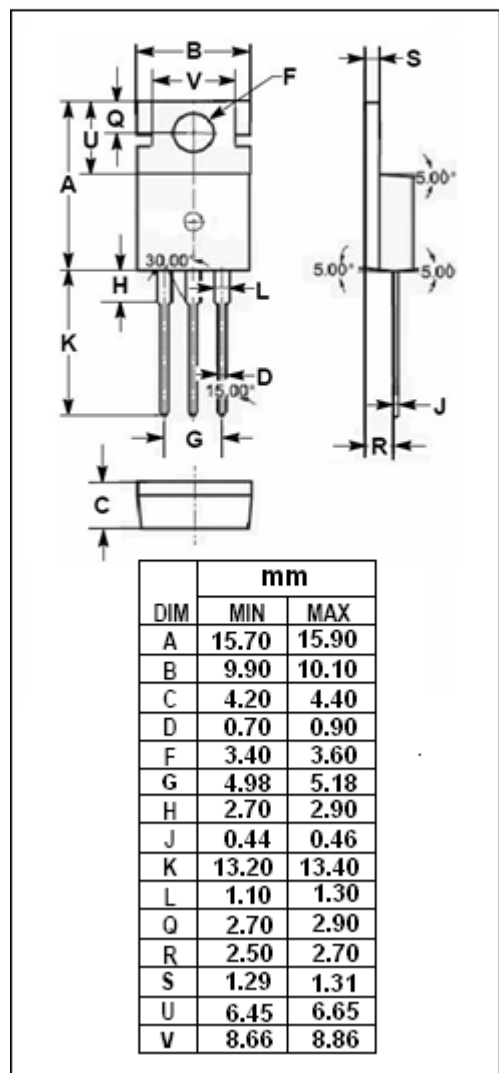
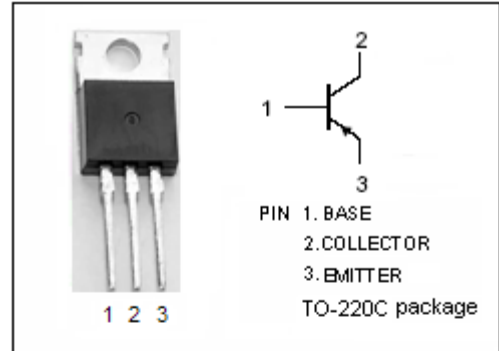
- Designed for a wide variety of medium-power switching and amplifier applications , such as series and shunt regulators and driver and output stages of high-fidelity amplifiers.

**ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	-60	V
$V_{CEO}$	Collector-Emitter Voltage	-60	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_C$	Collector Current-Continuous	-8	A
$I_B$	Base Current-Continuous	-3	A
$P_C$	Collector Power Dissipation $T_c=25^\circ\text{C}$	65	W
$T_j$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Ttemperature Range	-55~150	$^\circ\text{C}$

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	1.92	$^\circ\text{C/W}$



**isc Silicon PNP Power Transistor****BD798****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C = -100\text{mA}; I_B = 0$	-60			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -3\text{A}; I_B = -0.3\text{A}$			-1	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C = -3\text{A}; V_{CE} = -2\text{V}$			-1.6	V
$I_{CBO}$	Collector Cutoff Current	$V_{CB} = -60\text{V}; I_E = 0$			-0.1	mA
$I_{EBO}$	Emitter Cutoff Current	$V_{EB} = -5\text{V}; I_C = 0$			-1	mA
$h_{FE-1}$	DC Current Gain	$I_C = -1\text{A}; V_{CE} = -2\text{V}$	40			
$h_{FE-2}$	DC Current Gain	$I_C = -3\text{A}; V_{CE} = -2\text{V}$	25			
$f_T$	Current-Gain—Bandwidth Product	$I_C = -0.25\text{A}; V_{CE} = -10\text{V}, f_{test} = 1\text{MHz}$	3			MHz